



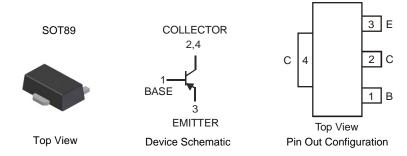
PNP SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Weight: 0.055 grams (approximate)



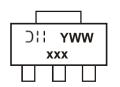
Ordering Information (Note 3)

Part Number	Case	Packaging
DCX69-13	SOT89	2500/Tape & Reel
DCX69-16-13	SOT89	2500/Tape & Reel
DCX69-25TA	SOT89	1000/Tape & Reel
DCX69-25-13	SOT89	2500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



xxx = Product Type Marking Code:
P12 = DCX69
P12-16 = DCX69-16
P12-25 = DCX69-25
YWW = Date Code Marking
Y = Last digit of year (ex: 7 = 2007)
WW = Week code (01 - 53)



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	Ic	-1.0	А
Peak Pulse Power	I _{CM}	-2.0	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	P_{D}	1	W
Thermal Resistance, Junction to Ambient Air @ T _A = 25°C (Note 4)	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

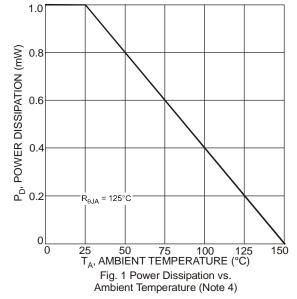
Characteristic		Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERIS	,						
Collector-Base Breakdown Voltage		V _{(BR)CBO}	-25	_	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage		V _{(BR)CEO}	-20	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-5.0	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Doog Cutoff Current		Ісво	_	_	-100	nA	$V_{CB} = -25V, I_{E} = 0$
Collector-base Cutor	Collector-Base Cutoff Current				-10	μΑ	$V_{CB} = -25V$, $I_E = 0$, $T_A = 150$ °C
Emitter-Base Cutoff (Current	I _{EBO}		_	-100	nA	$V_{EB} = -5.0V, I_{C} = 0$
ON CHARACTERIST	TICS (Note 5)						
	DCX69, DCX69-16, DCX69-25	h _{FE}	50	_	_	_	$V_{CE} = -10V, I_{C} = -5.0mA$
			60	_	_	_	$V_{CE} = -1.0V, I_{C} = -1.0A$
DC Current Gain	DCX69		85	_	375	_	$V_{CE} = -1.0V, I_{C} = -500mA$
	DCX69-16		100	_	250	_	$V_{CE} = -1.0V, I_{C} = -500mA$
	DCX69-25		160	_	375	_	$V_{CE} = -1.0V, I_{C} = -500mA$
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$		_	-0.5	V	$I_C = -1.0A$, $I_B = -100mA$
Base-Emitter Turn-On Voltage		V _{BE(ON)}	_	_	-0.7	V	$V_{CE} = -10V, I_{C} = -5mA$
				_	-1.0		$V_{CE} = -1.0V, I_{C} = -500mA$
SMALL SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product		f _T	40	200	_	MHz	$V_{CE} = -5.0V, I_{C} = -50mA,$ f = 100MHz
Output Capacitance		C _{obo}	_	17	_	pF	V _{CB} = -10V, f = 1MHz

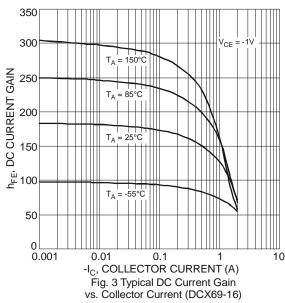
Notes:

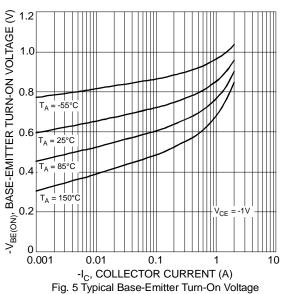
^{4.} Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.

5. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.



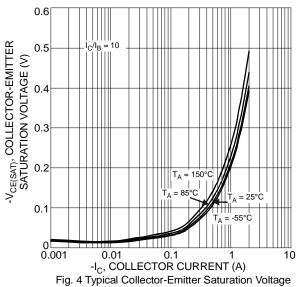






vs. Collector Current

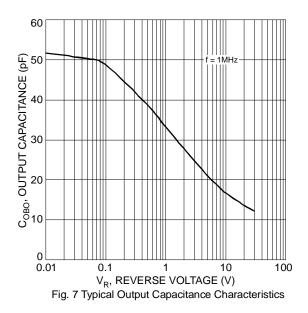
1.8

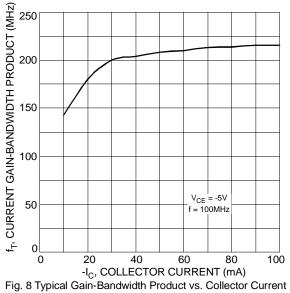


vs. Collector Current

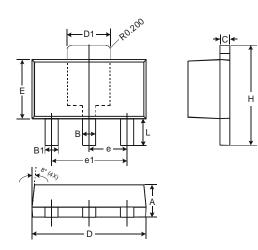
Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current





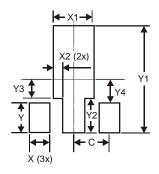


Package Outline Dimensions



SOT89			
Dim	Min	Max	
Α	1.40	1.60	
В	0.44	0.62	
B1	0.35	0.54	
С	0.35	0.43	
D	4.40	4.60	
D1	1.52	1.83	
Е	2.29	2.60	
е	1.50 Typ		
e1	3.00 Typ		
Н	3.94	4.25	
L	0.89	1.20	
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500

April 2012



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